Icemos Technology Ltd Product Specification 1000.547001 Issue Date 22 August 2018 17:40

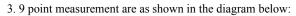
Part Number Customer	
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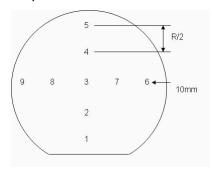
Category	Parameter		Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.30 mm	
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	402.00 +/- 4.10 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00μm	Guaranteed by Process
	7.0	Bow	<60.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	3mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	200.00 +/- 2.00 μm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Phosphorous	Wafer Vendor
	16.0	Handle Resistivity	1 ~ 10 Ohmem	Wafer Vendor
	17.0	Handle Oxygen Concentration	<12.60ppma	Wafer vendor
	18.0	Backside Finish	Polished with lasermark and NO oxide. Light handling marks.	Guaranteed by process
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	24.0	Nominal Thickness	200.00 +/- 2.00 μm	ADE Single point, 100%
	25.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by process
	26.0	Device Doping Type	N	Wafer Vendor
	27.0	Device Dopant	Phosphorous	Wafer Vendor
	28.0	Device Resistivity	1 ~ 10 Ohmcm	Wafer Vendor
	29.0	Oxygen Concentration	<12.60ppma	Wafer Supplier
	30.0	Voids	All wafers scanned for voids by Scanning Acoustic Microscope (SAM)	SAM & Bright Light, 100% (note 2)
	31.0	Scratches	0	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)

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Part Number		Customer	
Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspec	tion performed using microscope scan as below. 5x objective.	
		pections performed exclude all wafer area outside the edge exclusion	on defined in Overall

Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information